

IN THE CLAIMS:

No claims have been amended herein. All of the pending claims 1 through 7 are presented below. This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (Previously Presented) A method of forming a semiconductor device assembly, said method comprising:  
providing a substrate having an upper surface and a lower surface;  
depositing a layer of copper on one surface of the upper surface and the lower surface of the substrate;  
 patterning the layer of copper on the one surface of the upper surface and the lower surface of the substrate to form at least one bond pad thereon;  
depositing at least one layer of metal on at least a portion of the layer of copper; and  
connecting one end of a conductor lead of a TAB tape to the at least one layer of metal.

2. (Previously Presented) The method of claim 1, further comprising:  
connecting one end of the conductor lead of the TAB tape to the at least one layer of metal using a wire bond.

3. (Previously Presented) A method of forming a semiconductor device assembly, said method comprising:  
providing a substrate having an upper surface and a lower surface;  
depositing a layer of copper on the one surface of the upper surface and the lower surface of the substrate;  
 patterning the layer of copper on one surface of the upper surface and the lower surface of the substrate to form at least one bond pad thereon;

depositing at least one layer of gold metal on at least a portion of the layer of copper; and connecting one end of a conductor lead of a TAB tape to the at least one layer of gold metal.

4. (Previously Presented) A method of forming a semiconductor device assembly having a substrate having an upper surface and a lower surface, said method comprising: depositing a layer of copper on one surface of the upper surface and the lower surface of the substrate; patterning the layer of copper on the one surface of the upper surface and the lower surface of the substrate to form at least one bond pad thereon; depositing at least one layer of metal on at least a portion of the layer of copper; and connecting one end of a conductor lead of a TAB tape to the at least one layer of metal.

5. (Previously Presented) The method of claim 4, further comprising: connecting one end of the conductor lead of the TAB tape to the at least one layer of metal using a wire bond.

6. (Previously Presented) A method of forming a semiconductor device assembly having a substrate having an upper surface and a lower surface, said method comprising: depositing a layer of copper on one surface of the upper surface and the lower surface of the substrate; patterning the layer of copper on the one surface of the upper surface and the lower surface of the substrate to form at least one bond pad thereon; depositing at least one layer of gold metal on at least a portion of the layer of copper; and connecting one end of a conductor lead of a TAB tape to the at least one layer of gold metal.

7. (Previously Presented) A method of forming a semiconductor device assembly having a substrate having an upper surface and a lower surface, said method comprising: depositing a layer of copper on one surface of the upper surface and the lower surface of the substrate;

patterning the layer of copper on the one surface of the upper surface and the lower surface of the substrate to form at least one bond pad thereon;

depositing at least one layer of gold metal on at least a portion of the layer of copper; and connecting one of an end of a conductor lead of a TAB tape and a portion of a bond wire to the at least one layer of gold metal.